

A1  
an insulating layer formed in at least the outer circumferential portion of the molding portion and also in the upper portion of the electrode layer,

a conductive layer formed in the molding portion, and

a cover member for covering the conductive layer and the insulating layer in a separable manner.

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A2  
3. (Amended) The electrode structure for the iontophoresis device according to claim 1, wherein the sinking depth in the molding portion of the substrate film is in a range of 0.5 mm to 7.5 mm.

4. (Amended) The electrode structure for the iontophoresis device according to claim 1, wherein the molding angle in the molding portion of the substrate film is in a range of 5° to 70°.

5. (Amended) The electrode structure for the iontophoresis device according to claim 1, wherein the cover member is to seal the conductive layer between the insulating layer and itself in a separable manner, thereby allowing the conductive layer to be kept in a sealed state.

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A3  
13. (Amended) The method of producing the electrode structure for the iontophoresis device according to claim 11, wherein the method further comprises a step of supplying an adhesive sheet to the rear face of the substrate film and cutting the sheet into a predetermined shape.

14. (Amended) The method of producing the electrode structure for the iontophoresis device according to claim 11, wherein the step